# Low VCE (sat) Bipolar Transistor (PNP)NPN, (–)50V, (–)2A

#### Features

- Adoption of MBIT Process
- Large Current Capacity
- Low Collector to Emitter Saturation Voltage
- High Speed Switching
- Ultrasmall Package Facilitates Miniaturization in End Products (mounting height : 0.9mm)
- High Allowable Power Dissipation

### **Typical Applications**

- Relay Drivers
- Lamp Drivers
- Motor Drivers
- Flash

### **SPECIFICATIONS** (): CPH3145

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)							
Parameter	Symbol	Value	Unit				
Collector to Base Voltage	VCBO	(–50)80	V				
Collector to Emitter Voltage	VCES	(-50)80	V				
Collector to Emitter Voltage	VCEO	(–)50	V				
Emitter to Base Voltage	VEBO	(–)6	V				
Collector Current	IC	(–)2	А				
Collector Current (Pulse)	ICP	(–)4	А				
Base Current	IB	(–)400	mA				
Collector Dissipation When mounted on ceramic substrate ( $600mm^2 \times 0.8mm$ )	PC	0.9	V				
Junction Temperature	Tj	150	°C				
Storage Temperature	Tstg	-55 to +150	°C				

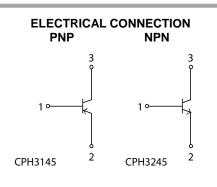
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Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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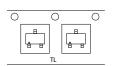
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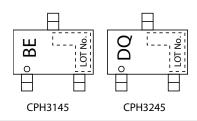


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#### PACKING TYPE : TL



#### MARKING



**ORDERING INFORMATION** See detailed ordering and shipping

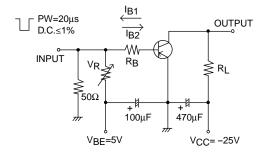
information on page 5 of this data sheet.

#### **ELECTRICAL CHARACTERISTICS** at $Ta = 25^{\circ}C$ (Note 2)

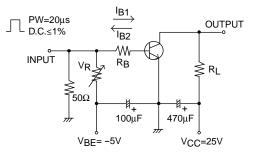
Parameter	Cumb al	Conditions	Value			Unit
Parameter	Symbol Conditions		min	typ	max	Unit
Collector Cutoff Current	ICBO	V <sub>CB</sub> =(-)40V, I <sub>E</sub> =0A			(–)1	μA
Emitter Cutoff Current	IEBO	VEB=(-)4V, IC=0A		(–)1	μA	
DC Current Gain	hFE	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)100mA 200		560		
Gain-Bandwidth Product	fT	VCE=(-)10V, IC=(-)300mA		420		MHz
Output Capacitance	Cob	VCB=(-)10V, f=1MHz		(16)8		pF
Collector to Emitter Saturation Voltage	V <sub>CE</sub> (sat)	IC=(-)1A, IB=(-)50mA		(–165)130	(-330)260	mV
Base to Emitter Saturation Voltage	V <sub>BE</sub> (sat)			(–)0.9	(–)1.2	V
Collector to Base Breakdown Voltage	V(BR)CBO	IC=(-)10μΑ, IE=0Α	(-50)80			V
Collector to Emitter Breakdown Voltage	V(BR)CES	IC=(-)100μA, RBE=0Ω	(-50)80			V
Collector to Emitter Breakdown Voltage	V(BR)CEO	IC=(−)1mA, RBE=∞	(–)50			V
Emitter to Base Breakdown Voltage	V(BR)EBO	IE=(-)10μΑ, IC=0Α	(–)6			V
Turn-ON Time	ton			(35)35		ns
Storage Time	tstg	See specified Test Circuit		(200)330		ns
Fall Time	tf			(24)40		ns

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

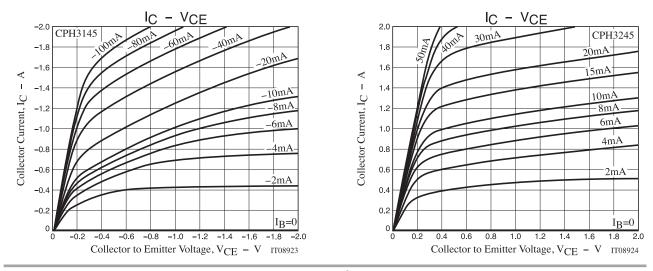
#### Switching Time Test Circuit



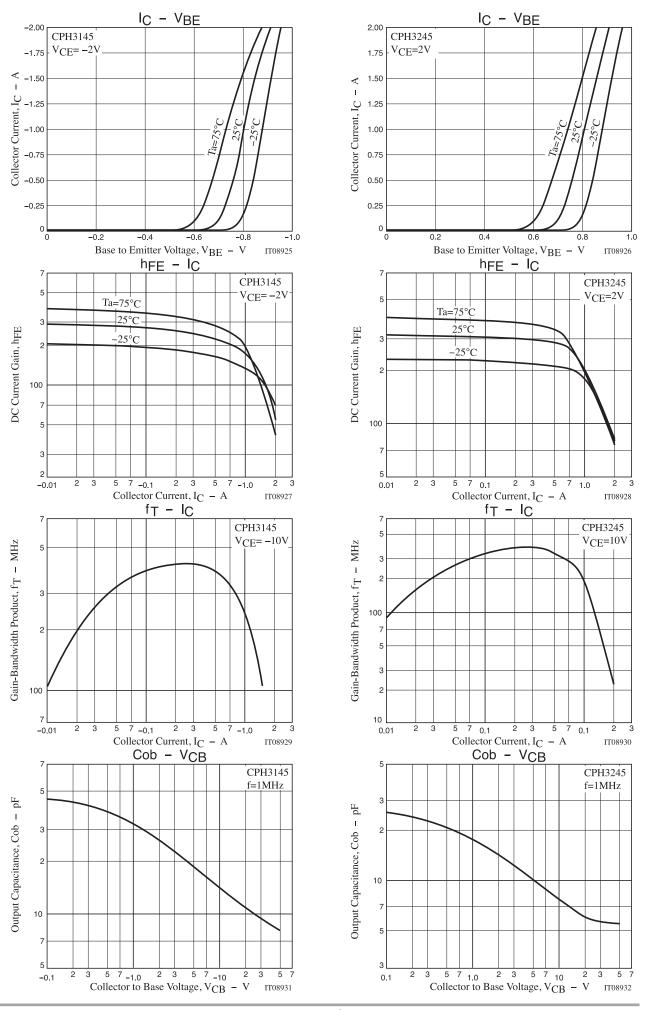
 $I_{C}$ = -10 $I_{B1}$ =10 $I_{B2}$ = -0.7A CPH3145



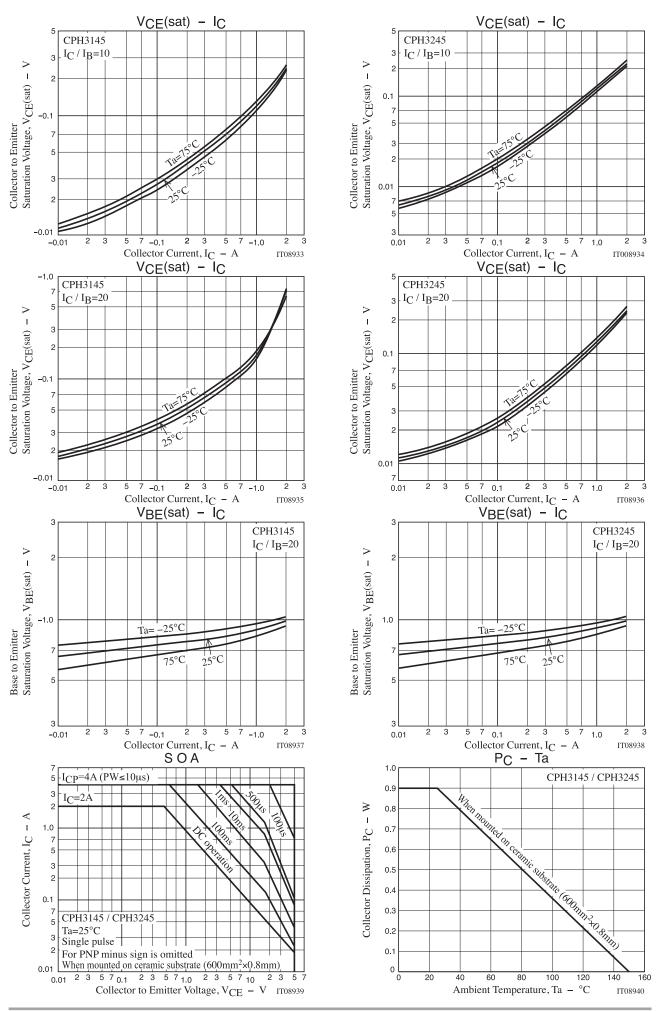
 $I_{C}=10I_{B1}=-10I_{B2}=0.7A$ CPH3245



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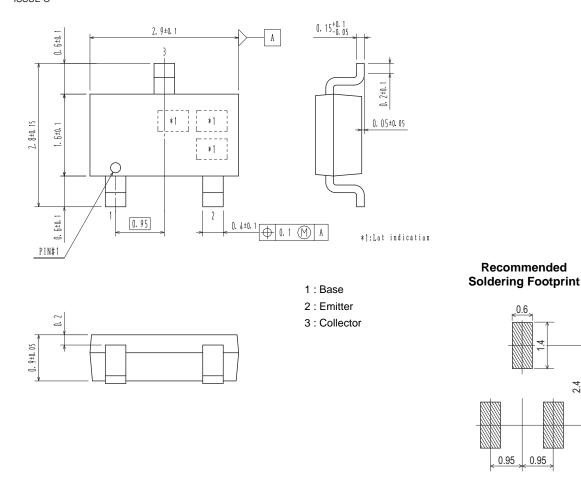


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#### PACKAGE DIMENSIONS

#### unit : mm

СРНЗ CASE 318BA ISSUE O



#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping (Qty / Packing)
CPH3145-TL-E	BE	CPH3 SC-59, SOT-23, TO-236	3.000 / Tape & Reel
CPH3245-TL-E	DQ	(Pb-Free)	5,000 / Tape & Reel

2.4

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

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